



**TO-92MOD Plastic-Encapsulate Transistors**

**2SC3243** TRANSISTOR (NPN)

**FEATURES**

Power dissipation

$P_{CM}$ : 0.9 W ( $T_{amb}=25^{\circ}C$ )

Collector current

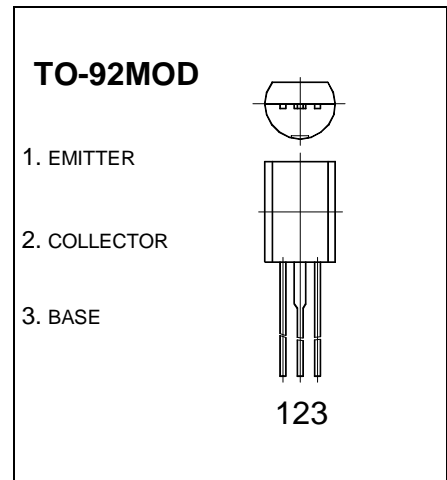
$I_{CM}$ : 1 A

Collector-base voltage

$V_{(BR)CBO}$ : 60 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$  unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50V, I_E=0$			0.2	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			0.2	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=4V, I_C=100mA$	55		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=25mA$			0.3	V
Transition frequency	$f_T$	$V_{CE}=2V, I_C=10mA$	80			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		25		pF

**CLASSIFICATION OF  $h_{FE(1)}$**

Rank	C	D	E
Range	55-110	90-180	150-300
Marking			